

June 1995

File Number 1412

# 8A, 100V - 200V Ultrafast Dual Diodes

The BYW51 series devices are low forward voltage drop, ultra-fast-recovery rectifiers ( $t_{RR} < 35 ns$ ). They use a planar ion-implanted epitaxial construction.

These devices are intended for use as output rectifiers and fly-wheel diodes in a variety of high-frequency pulse-width-modulated and switching regulators. Their low stored charge and attendant fast reverse-recovery behavior minimize electrical noise generation and in many circuits markedly reduce the turn-on dissipation of the associated power switching transistors.

# **Ordering Information**

### **PACKAGING AVAILABILITY**

PART NUMBER	PACKAGE	BRAND
BYW51-100	TO-220AB	BYW51100
BYW51-150	TO-220AB	BYW51150
BYW51-200	TO-220AB	BYW51200

NOTE: When ordering, use the entire part number.

## **Features**

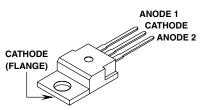
- Ultra Fast Recovery Time (<35ns)</li>
- Low Forward Voltage
- Low Thermal Resistance
- Planar Design
- Wire-Bonded Construction

# **Applications**

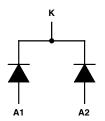
- General Purpose
- · Power Switching Circuits to 100kHz
- Full-Wave Rectification

## **Package**

### JEDEC TO-220AB



# Symbol



### Absolute Maximum Ratings Per Junction

	BYW51-100	BYW51-150	BYW51-200	UNITS
Maximum Peak Repetitive Reverse Voltage $\dots V_{RRM}$	100	150	200	V
Maximum Peak Surge VoltageV <sub>RSM</sub>	110	165	220	V
Repetitive Peak Surge Current $I_{FRM}$ , $t_P < 10 \mu s$	100	100	100	Α
Nonrepetitive Peak Surge Current $I_F(RMS)$ , Total	20	20	20	Α
Average Rectified forward Current $I_{F(AV)}$ , Total $T_C = +125^{\circ}C$ , $a = 0.5$	8	8	8	Α
Repetitive Peak Surge Current $I_{FSM}$ $t_P = 10$ ms, Sinusoidal	100	100	100	Α
Maximum Power Dissipation $P_D$ , $T_C = +125 \infty^0 C$	20	20	20	W
Operating and Storage Temperature	-40 + 150	-40 + 150	-40 + 150	°C
$T_L$ (Lead Temperature During Soldering) At Distance > $^{1}/_{8}$ in. (3.17mm) From Case For 10s max.	260	260	260	°C

# BYW51-100, BYW51-150, BYW51-200

# Electrical Specifications Per Junction

	TEST CONDITIONS		LIMITS							
	т.	VOLTAGE	CURRENT	BYW	51-100	BYW	51-150	BYW	51-200	1
SYMBOL	T <sub>J</sub> °C	V <sub>R</sub> V	i <sub>F</sub> A	MIN	MAX	MIN	MAX	MIN	MAX	UNITS
IR	25	100	-	-	5	-	-	-	-	μΑ
		150	-	-	-	-	5	-	-	μΑ
		200	-	-	-	-	-	-	5	μА
	100	100	-	-	1	-	-	-	-	mA
		150	-	-	-	-	1	-	-	mA
		200	-	-	-	-	-	-	1	mA
V <sub>F</sub>	25	-	8	-	0.95	-	0.95	-	0.95	٧
	100	-	8	-	0.89	-	0.89	-	0.89	٧
t <sub>RR</sub>	25	-	1 (Note 1)	-	35	-	35	-	35	ns
R <sub>0JC</sub> , Per Leg		-	-	-	2.5	-	2.5	-	2.5	°C/W
R <sub>0JC</sub> , Total		-	-	-	1.3	-	1.3	-	1.3	°C/W
$R_{\theta JA}$		-	-	-	60	-	60	-	60	°C/W
СЈ	25	10	0		•	All types	(typ.) 40		•	pF

NOTE:

<sup>1.</sup>  $dI_F/dt > 50A/\mu s$ ,  $I_{RM}(rec) < 1A$ ,  $I_{RR} = 0.25A$ .

# **Typical Performance Curves**

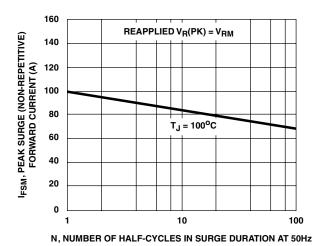


FIGURE 1. PEAK SURGE FORWARD CURRENT vs SURGE DURATION

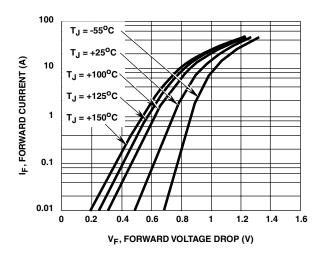


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

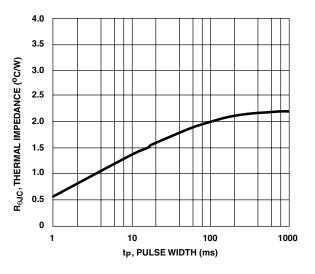


FIGURE 2. THERMAL IMPEDANCE vs PULSE WIDTH (PER JUNCTION)

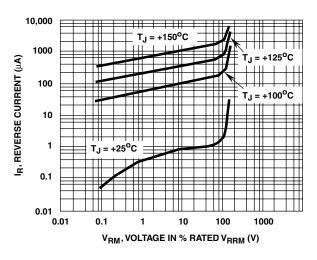


FIGURE 4. TYPICAL REVERSE CURRENT vs VOLTAGE

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